

FIG. 1A

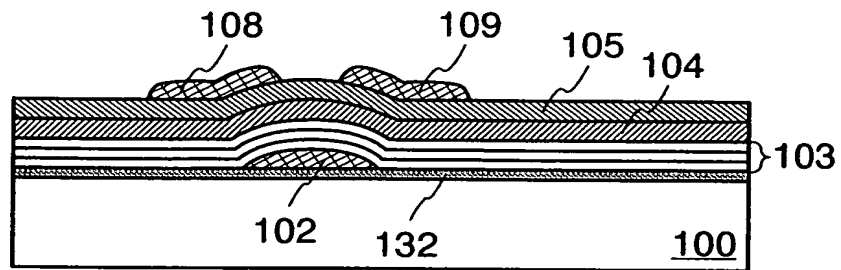


FIG. 1B

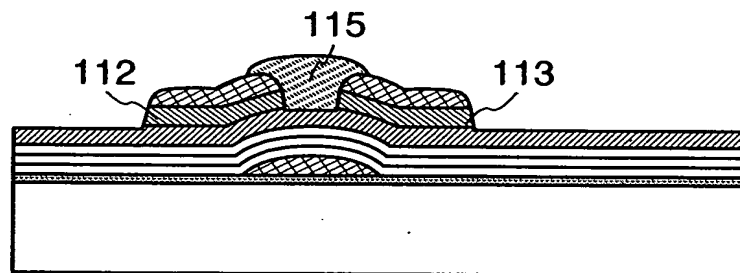


FIG. 1C

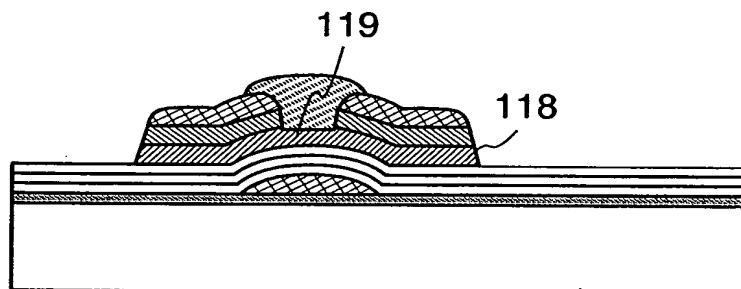


FIG. 1D

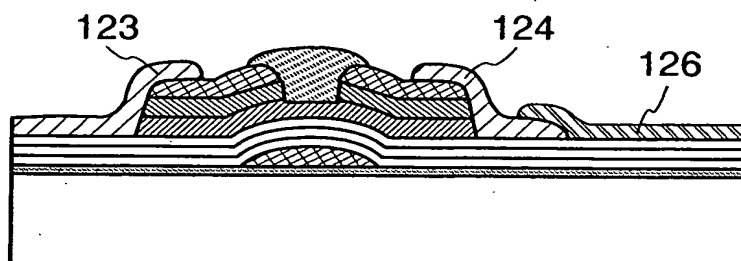


FIG. 2A

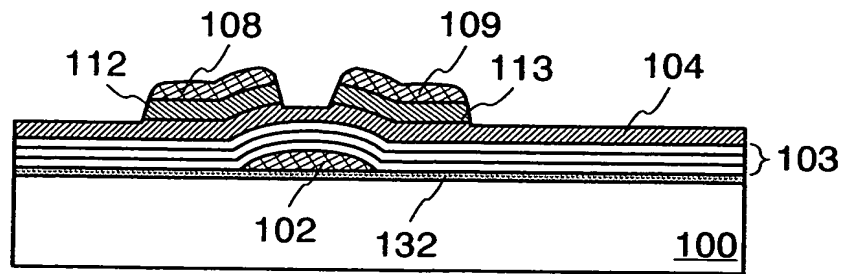


FIG. 2B

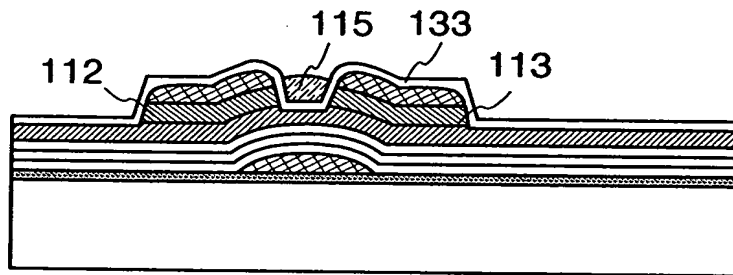


FIG. 2C

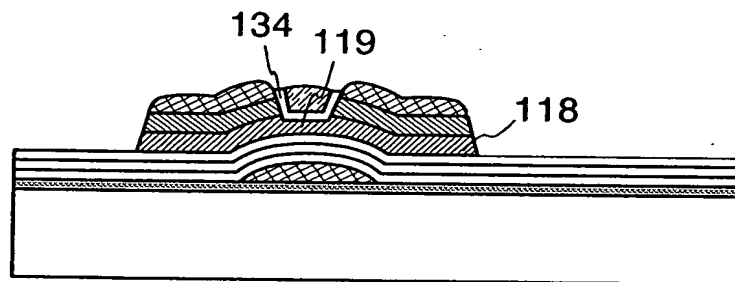


FIG. 2D

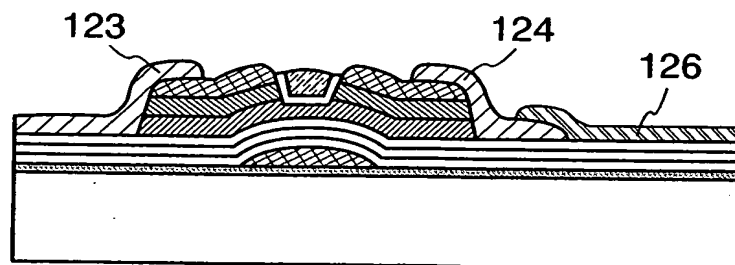


FIG. 3A

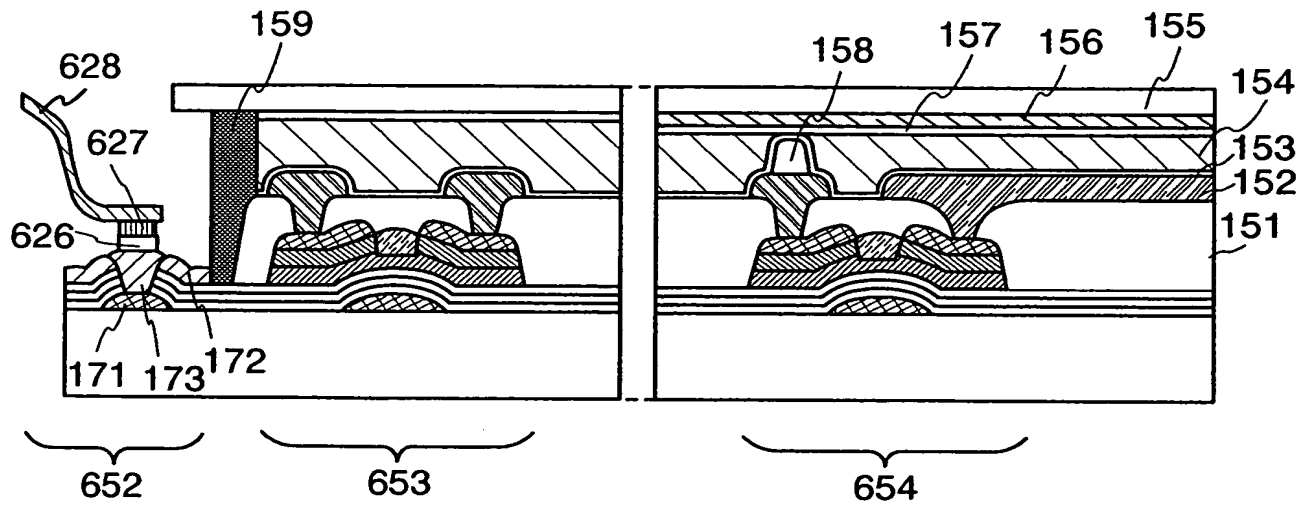


FIG. 3B

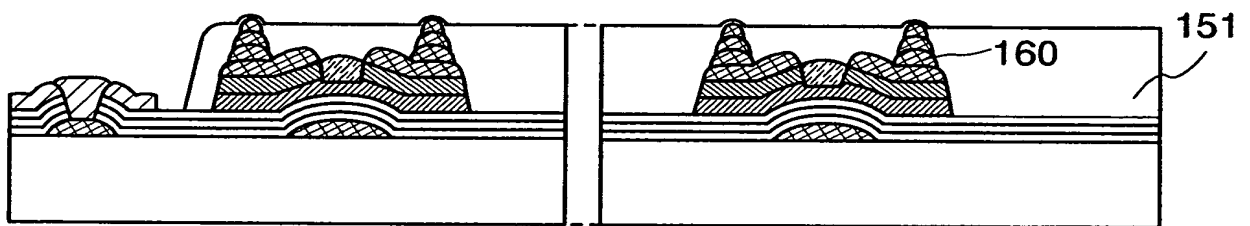


FIG. 3C

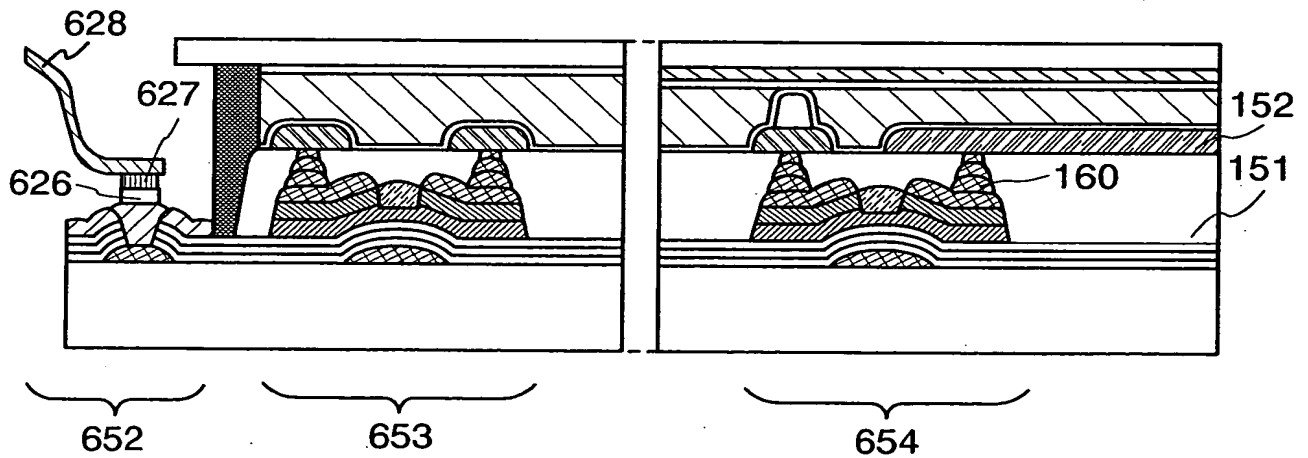


FIG. 4A

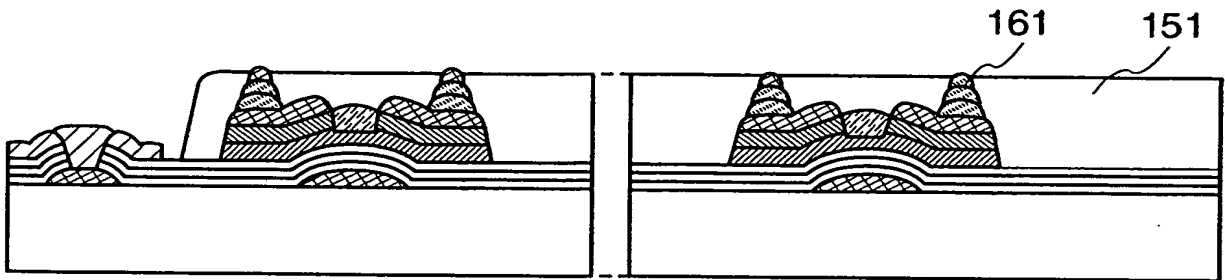


FIG. 4B

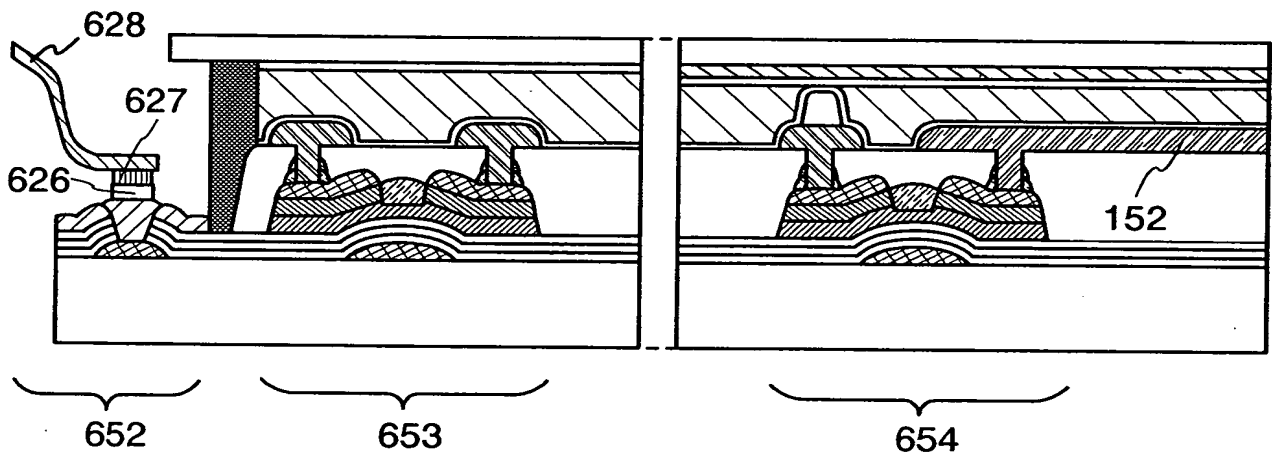


FIG. 5A

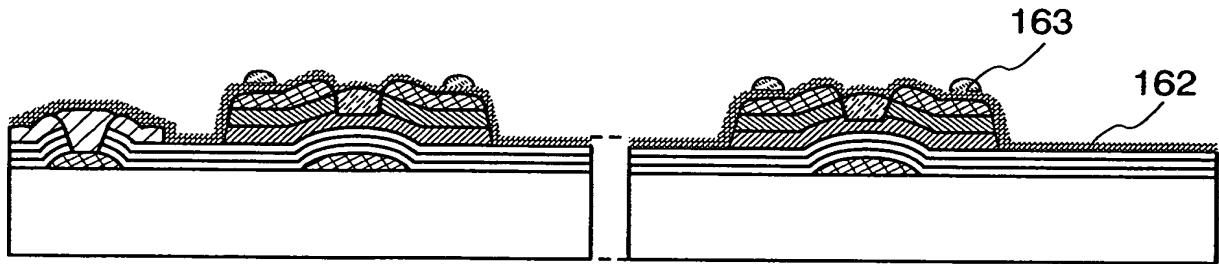


FIG. 5B

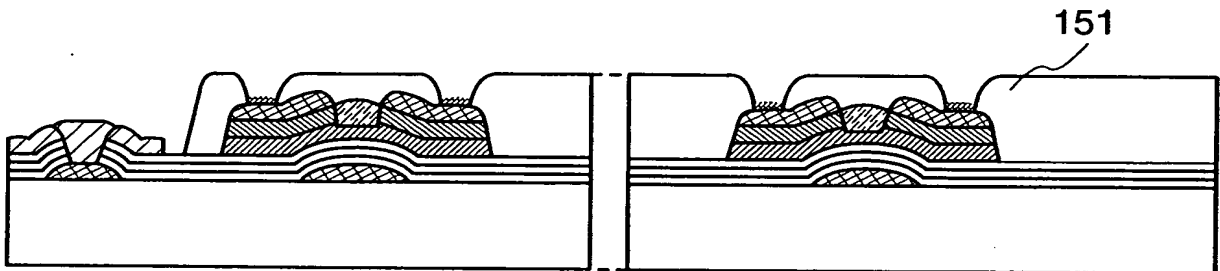


FIG. 5C

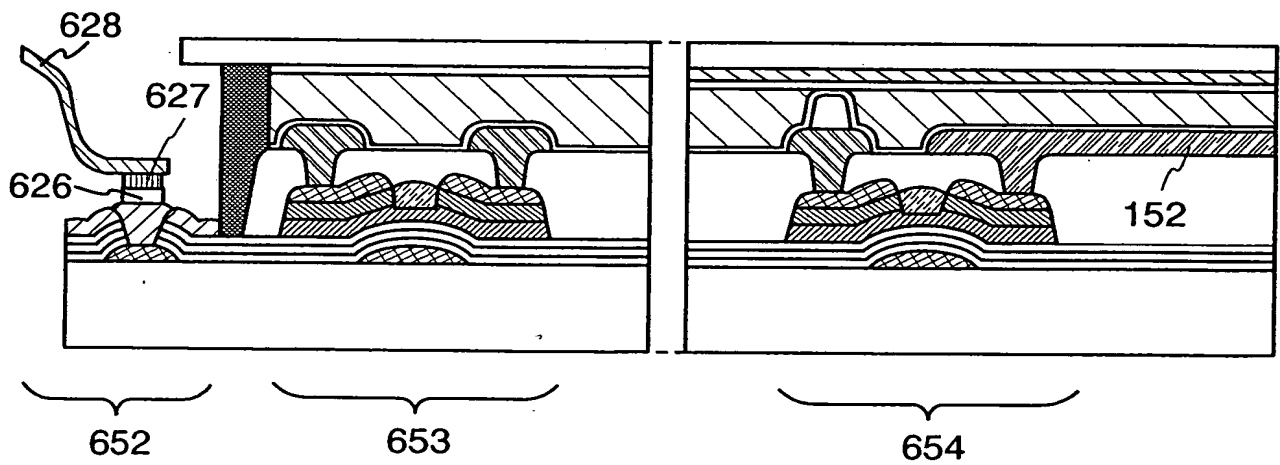


FIG. 6A

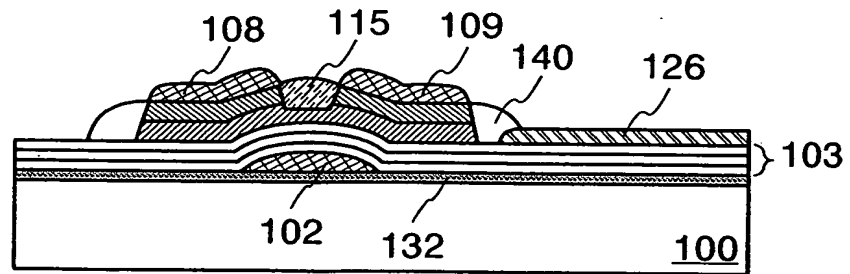


FIG. 6B

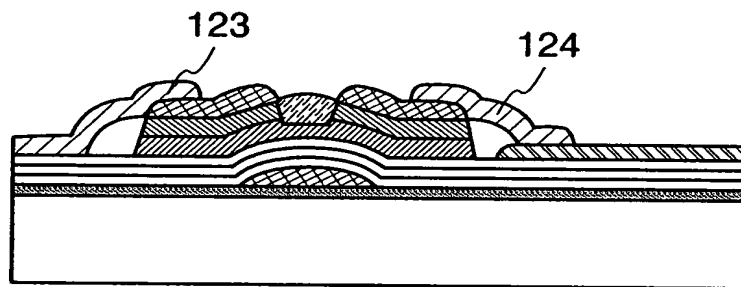


FIG. 6C

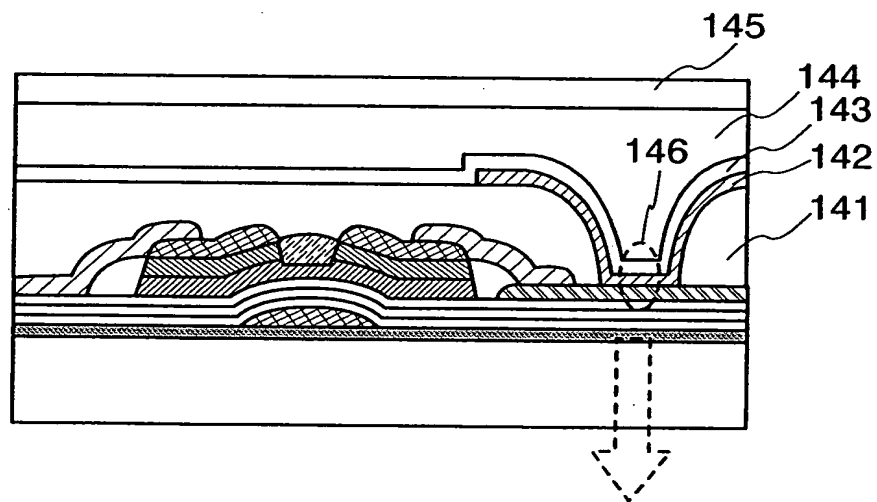


FIG. 7A

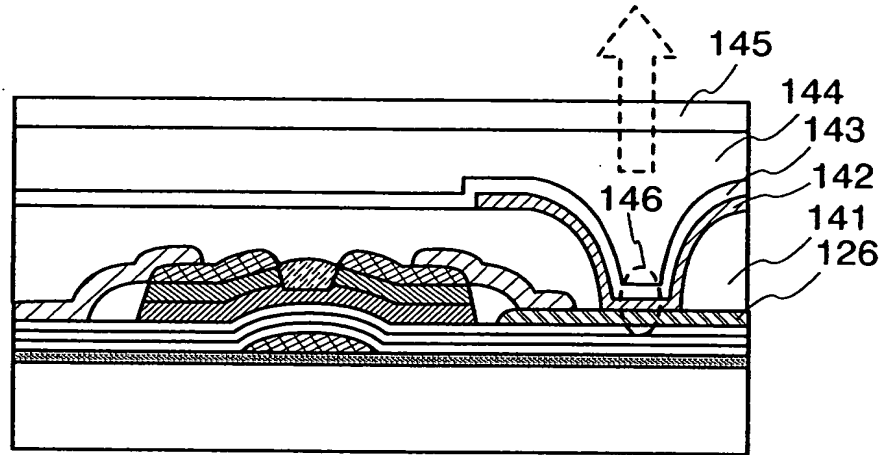


FIG. 7B

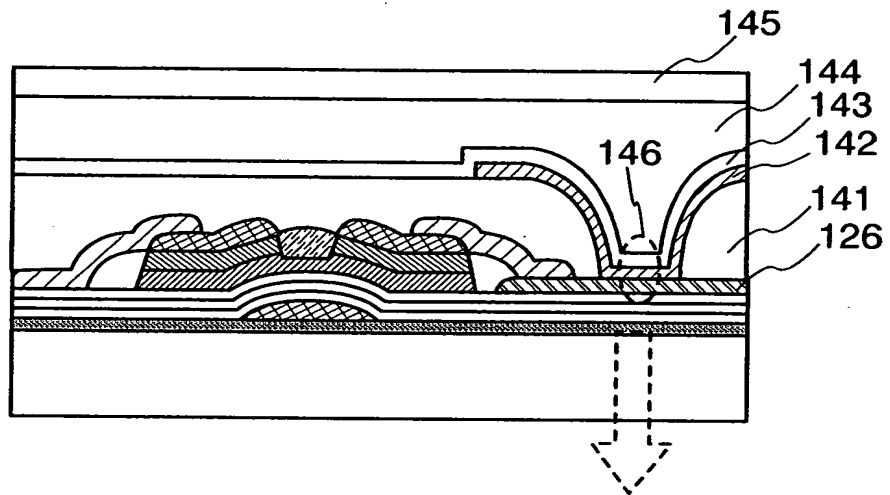


FIG. 7C

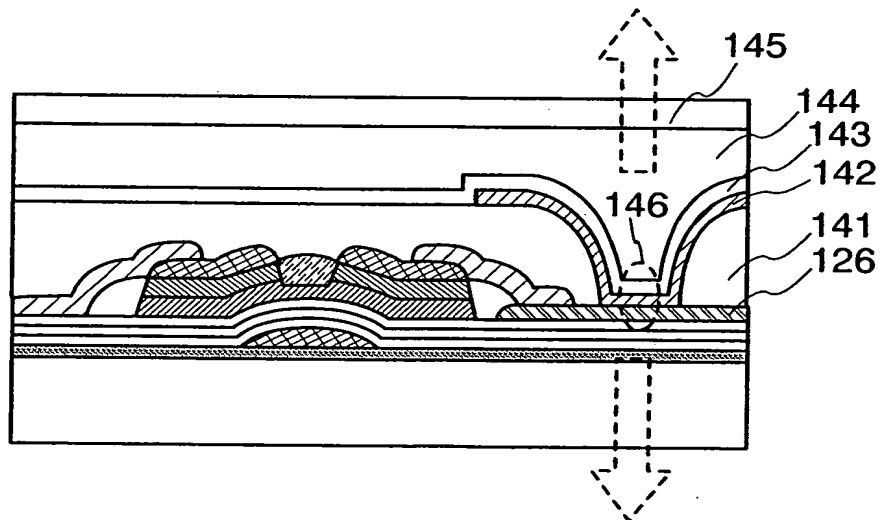
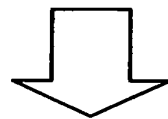
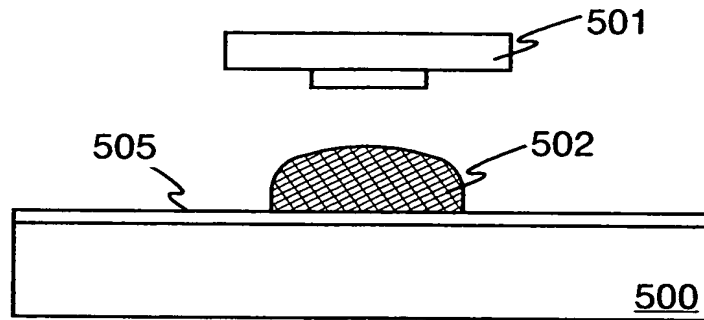
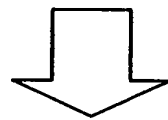
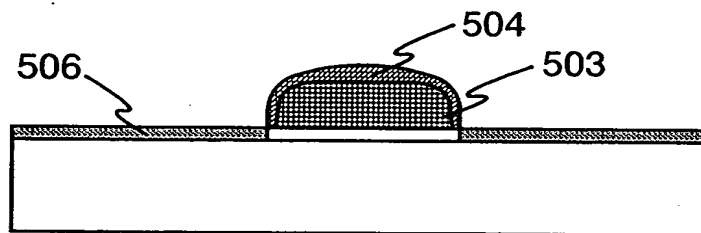


FIG. 8A



DRYING OR BAKING

FIG. 8B



BAKING UNDER  
ATMOSPHERE  
CONTAINING  
OXYGEN OR OXYGEN  
PLASMA TREATMENT

FIG. 8C

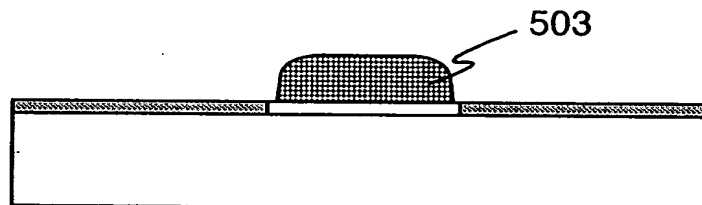


FIG. 9A

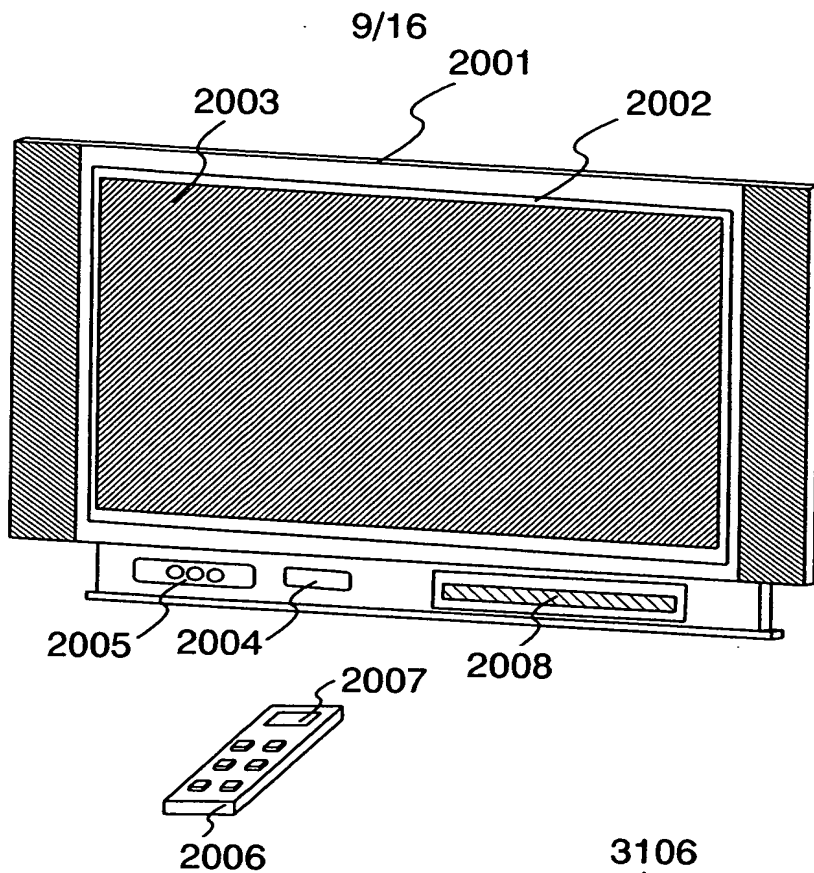


FIG. 9B

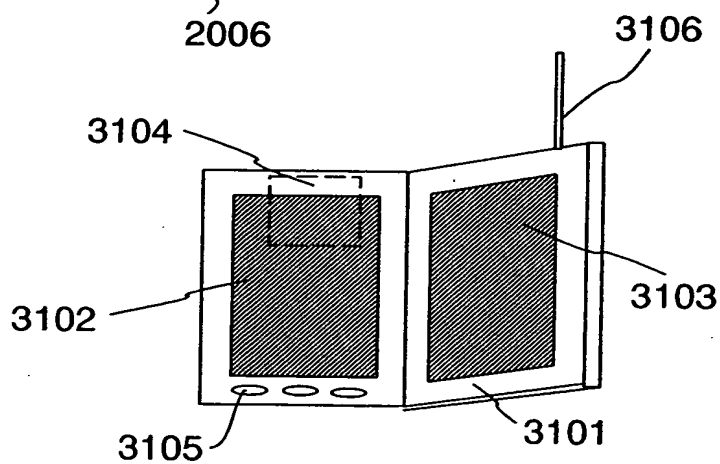


FIG. 9C

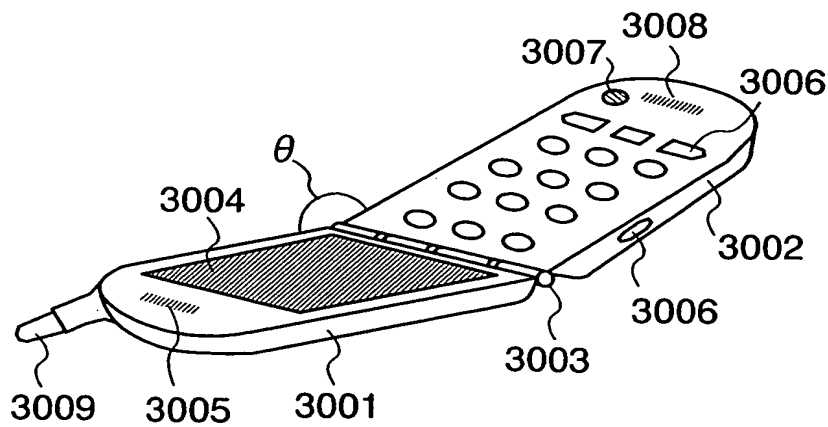


FIG. 10

The diagram illustrates a system for manufacturing a substrate. The system includes a computer 802 connected to a database 801, a storage unit 819, and a control unit 806. The computer 802 is also connected to a substrate transfer mechanism 803. The substrate transfer mechanism 803 includes a substrate 804, a transfer head 805, and a transfer arm 808. The substrate 804 is shown with a grid of cells 810, 811, 812, 813, 814, 815, 816, 817, 818, 819, 820, 821, 822, 823, 824. A coordinate system (X, Y) and an angle  $\theta$  are shown at the bottom. An arrow indicates the "SUBSTRATE TRANSFER DIRECTION".

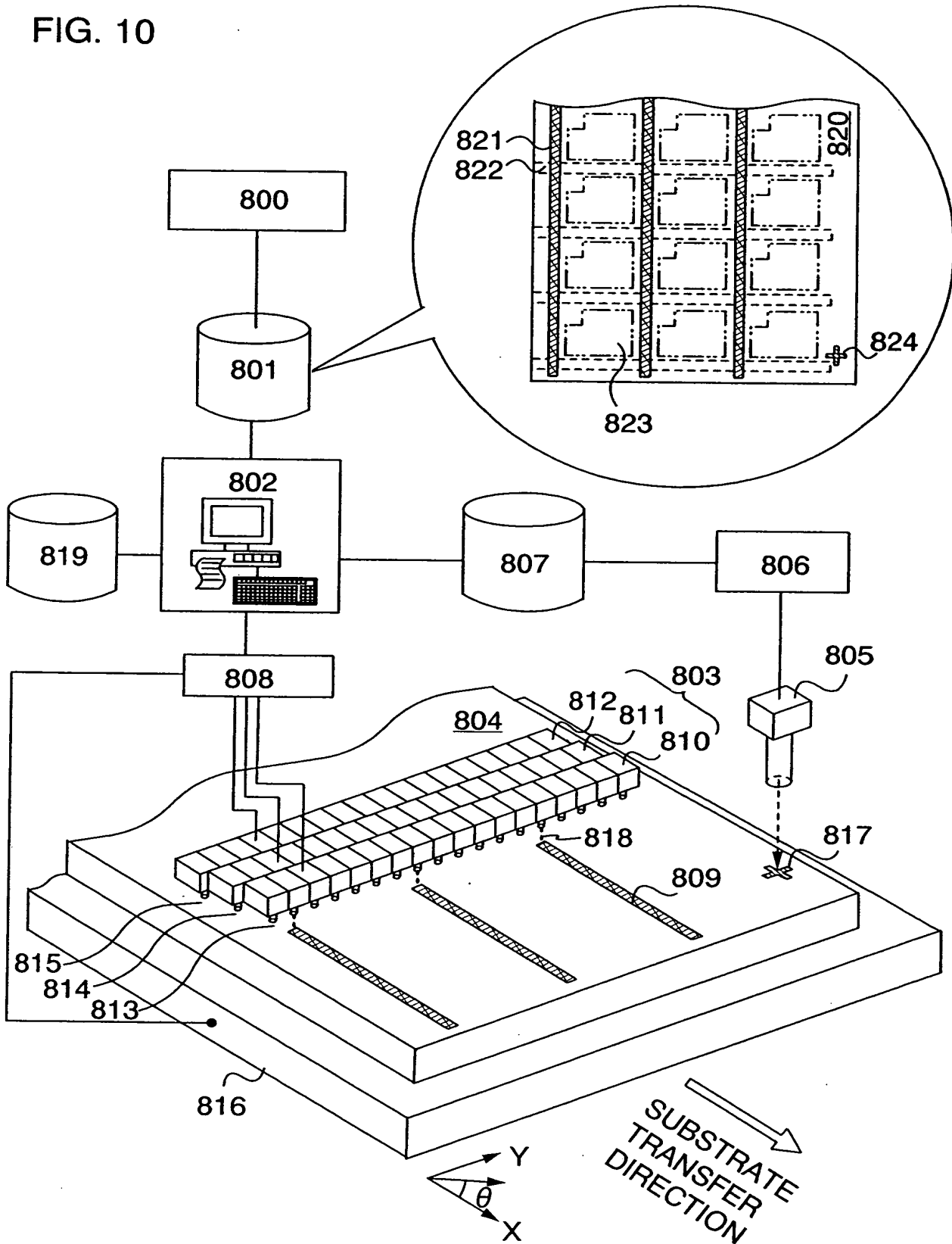


FIG. 11A

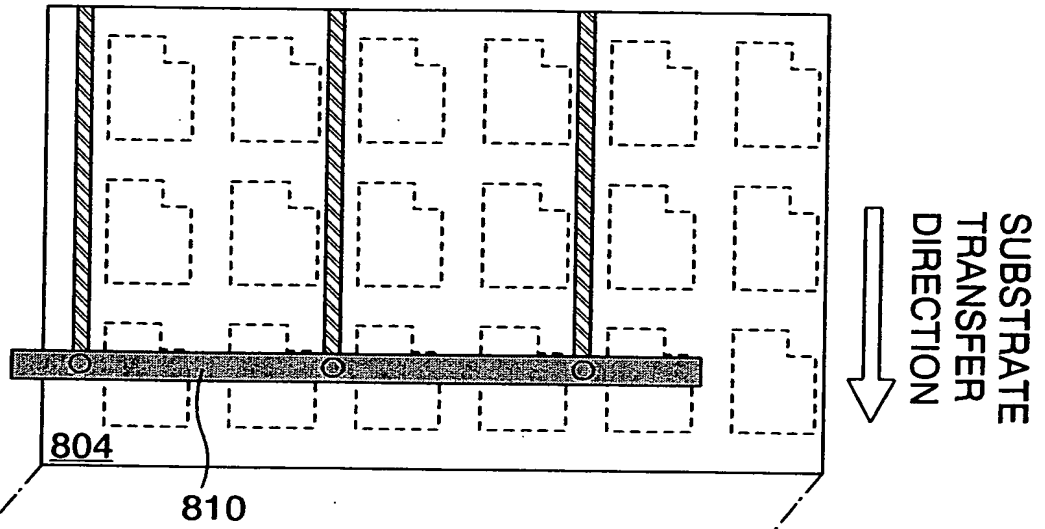


FIG. 11B

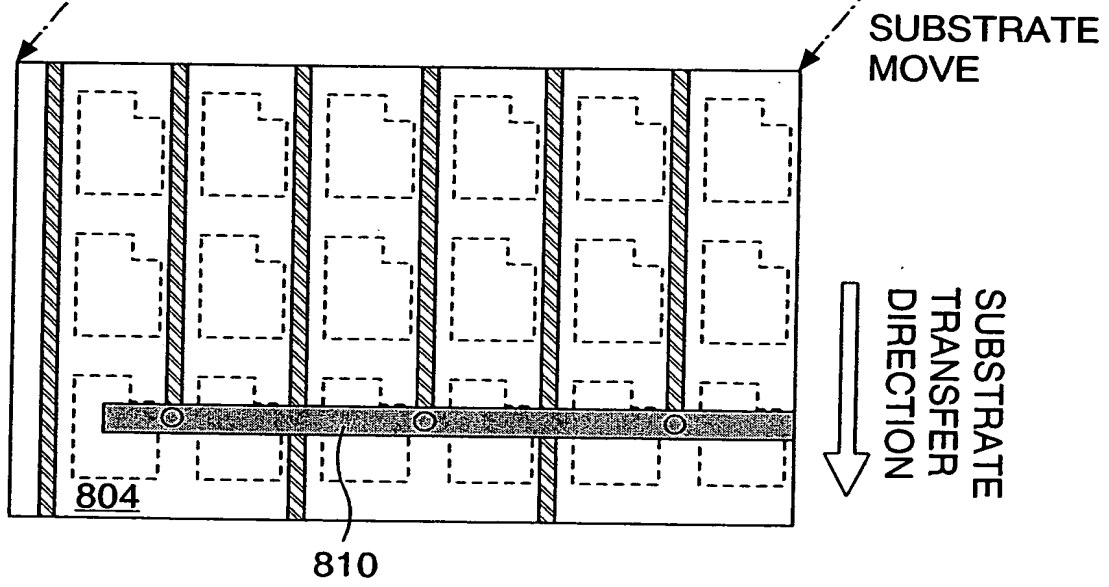


FIG. 12A

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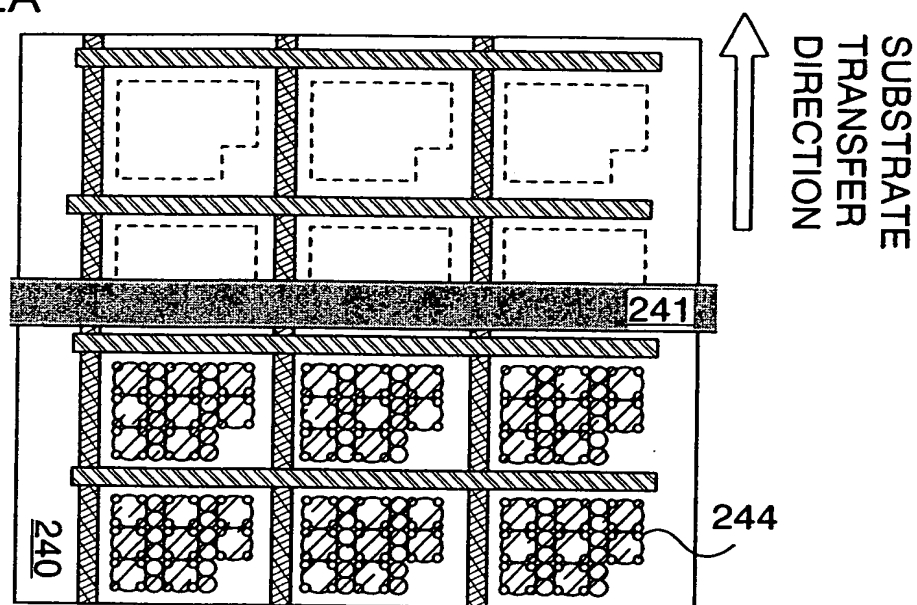


FIG. 12B

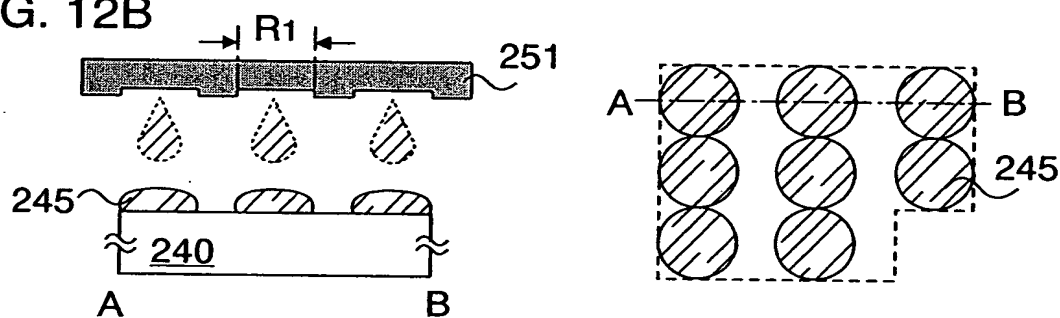


FIG. 12C

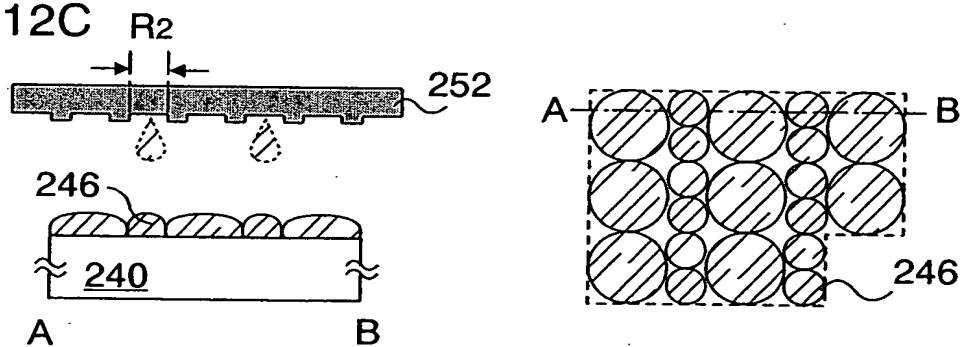


FIG. 12D

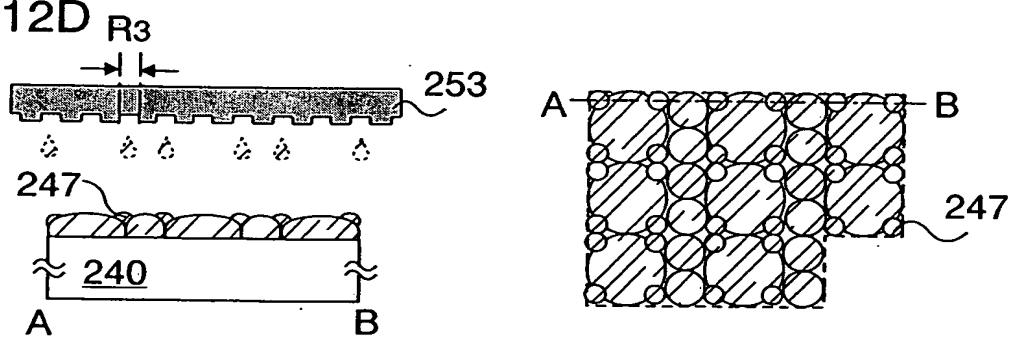


FIG. 13A

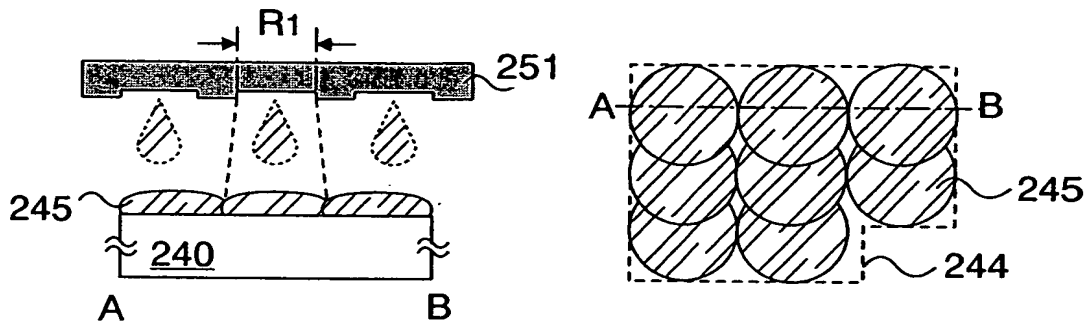


FIG. 13B

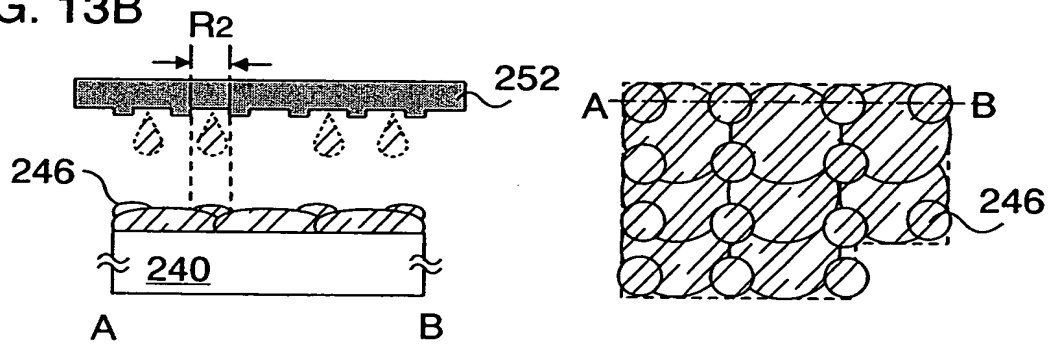


FIG. 13C

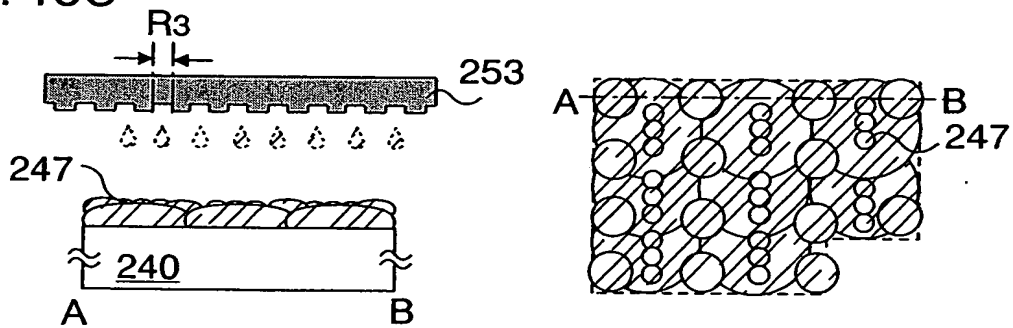


FIG. 14

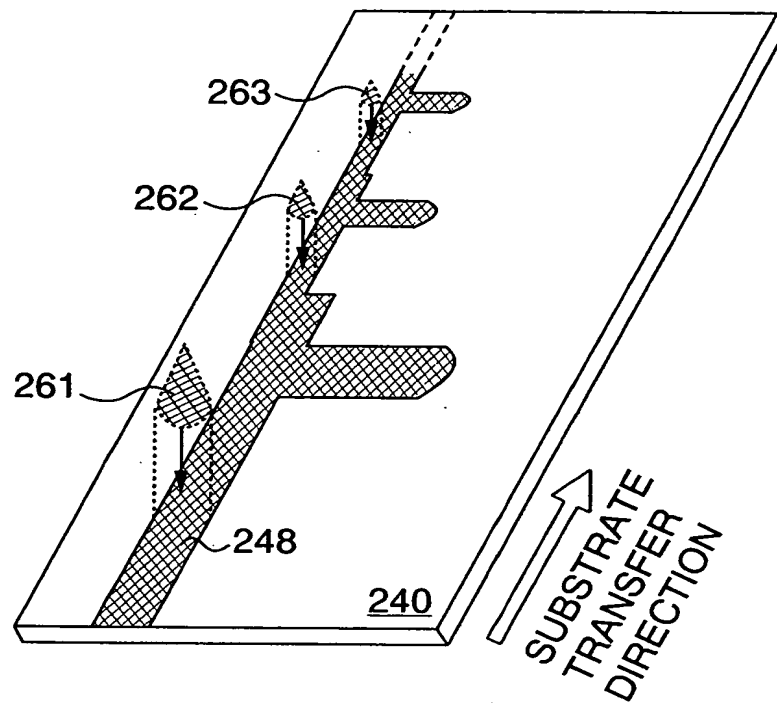


FIG. 15A

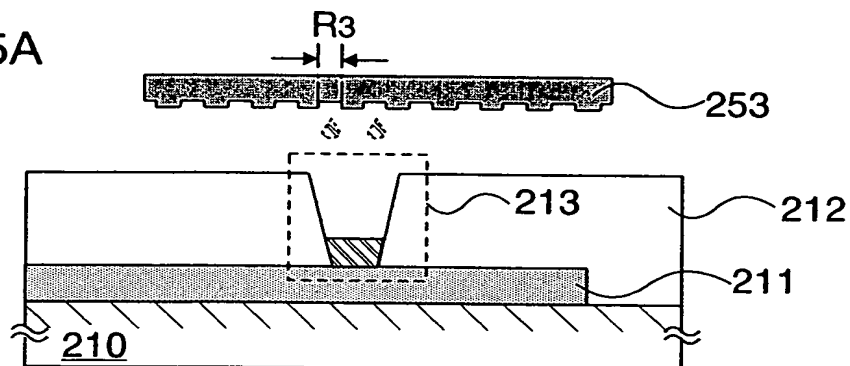


FIG. 15B

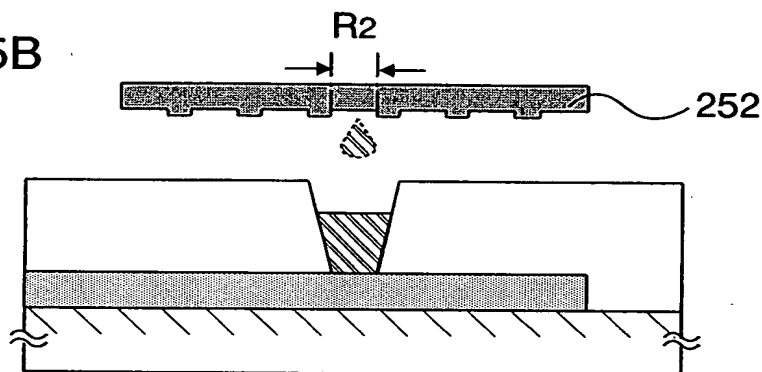
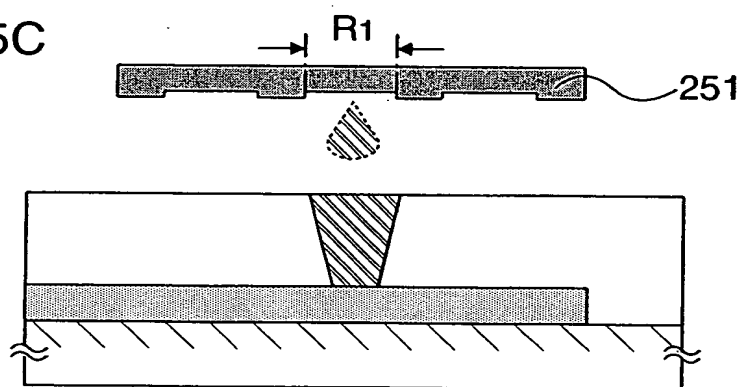


FIG. 15C



## [EXPLANATION OF REFERENCES]

100: Substrate, 102: Gate electrode layer, 103: Gate insulating film, 104: Semiconductor film, 105: N-type semiconductor film, 108: Source electrode, 109: Drain electrode, 112: Source region, 113: Drain region, 115: Insulating film, 118: Island-like semiconductor region, 119: Channel region, 123: Source wiring, 126: Pixel electrode, 132: Titanium oxide film, 134: Insulating film, 140: Insulator, 141: Bank, 142: Organic compound layer, 143: Electron injecting electrode, 144: Passivation film, 145: Opposing substrate, 146: Light-emitting element, 151: Planarization film, 152: Drain wiring, 153: Orientation film, 154: Liquid crystal layer, 155: Opposing substrate, 156: Transparent conductive film, 157: Orientation film, 158: Column-like spacer, 159: Sealant, 160: Column-like conductor, 161: Pillar insulator, 162: Liquid-shedding material, 163: Mask, 171: Wiring, 172: Conductor, 173: Conductor, 500: Glass substrate, 501: Nozzle, 502: Nano paste, 503: Conductor containing metal chains, 504: Film formed by organic ingredients, 626: Terminal electrode, 627: Anisotropic conductive film, 628: FPC, 652: Terminal portion, 654: Pixel TFT, 800: Circuit design tool, 801: Data of thin film pattern, 802: Computer, 805: Imaging means, 806: Image processing device, 807: Position information of alignment marker, 808: Controller, 816: XYθ stage, 817: Alignment marker, 819: Database, 2001: Housing, 2002: Display module, 2003: Main-screen, 2004: Modem, 2005: Receiver, 2006: Wireless remote control, 2007: Display portion, 2008: Sub-screen, 3001: Display panel, 3002: Operation panel, 3003: Connecting portion, 3004: Display portion, 3005: Voice output portion, 3006: Operation key, 3007: Power source switch, 3008: Voice input portion, 3009: Antenna, 3101: Main body, 3102: Display portion, 3103: Display portion, 3104: Memory medium, 3105: Operation switch, 3106: Antenna